

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

CS03-046

Application Number

10/743247

Applicant(s)

Tan

Filing Date

Group Art Unit

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RP		US 2003/0013260A1		Gossmann et al.			
RP		US 2003/0096490 A1		Borland, et al			
RP		US 2002/0001926 A1		Noda			
RP		US 6,537,886b2		Lee			
RP		US 2003/0049917 A1		Noda			
RP		US 6,475,885B1		Sultan			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

RP		Noda, "Evolution of end-of-range damage and transient enhanced diffusion of indium in Silicon", Journal of applied physics, vol 91, #2 15 Jan 2002, pp 639-645.
		Yeh et al., "Optimum halo structure for sub-0.1. m CMOSFETs, IEEE trans on electronic devices, vol. 48, # 10, Oct 2001, pp. 2357-2362.
RP		Lisebarger, et al., "Study of end of range loop interactions with B[sup +] implant damage using a boron doped diffusion layer", J. Appl. Phys. 78 (4), 15 August 1995, pp. 2298-2302.
		Lu et al., "Reduction of secondary defect formation in MeV B + ion-implanted Si(100)", Appl. pHys. Lett, 655 (18), 30 Oct 1989. pp. 1838 - 1840.

EXAMINER

[Signature]

DATE CONSIDERED

7/8/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.